

Silicon PNP Power Transistors

2N4907 2N4908 2N4909

DESCRIPTION

- With TO-3 package
- Excellent safe operating areas

APPLICATIONS

- For medium-speed switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

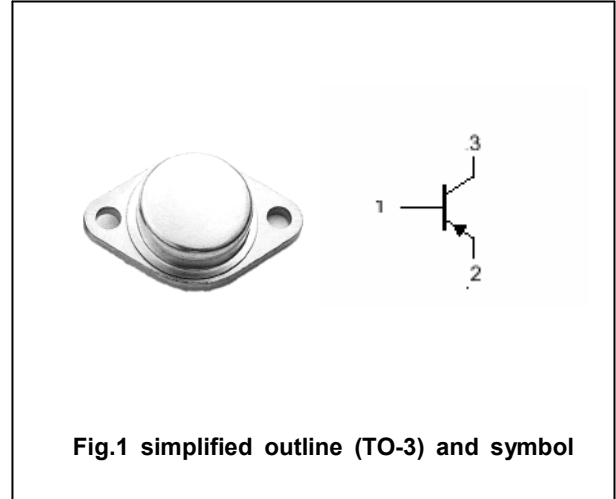


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N4907	-40	V
		2N4908	-60	
		2N4909	-80	
V _{CEO}	Collector-emitter voltage	2N4907	-40	V
		2N4908	-60	
		2N4909	-80	
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-10	A
I _B	Base current		-4	A
P _D	Total Power Dissipation	T _C =25℃	150	W
T _j	Junction temperature		200	℃
T _{stg}	Storage temperature		-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{(th) jc}	Thermal resistance junction to case	1.17	℃/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N4907	-40			V
		2N4908	-60			
		2N4909	-80			
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-1.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-1.5	V
V _{BE(on)}	Base-emitter on voltage	I _C =-4A; V _{CE} =-4V			-1.5	V
I _{CEX}	Collector cut-off current	V _{CE} =-100V; V _{BE(off)} =-1.5V T _C =150 °C			-1.0 -10.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V; I _C =0			-5.0	mA
h _{FE-1}	DC current gain	I _C =-4A; V _{CE} =-4V	20		80	
h _{FE-2}	DC current gain	I _C =-10A; V _{CE} =-4V	5			
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-10V	4			MHz

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.10mm)